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Tipo Comunicación para congreso

Fonte  2019 26th IEEE International Conference on Electronics, Circuits and Systems (ICECS) Génova (Italia), 2020.

DOI [10.1109/ICECS46596.2019.8964763](https://doi.org/10.1109/ICECS46596.2019.8964763)

Abstract A picowatt CMOS voltage reference for body implantable devices is presented in this paper. The circuit is based on a PMOS-only voltage reference core with a passive RC filter to enhance the supply noise rejection and a speed-up mechanism to improve the switching-on time of the circuit. The measured power consumption at a supply voltage of 0.7 V is as low as 64.5 pW at the reference human body temperature of 36 °C, with a PSR better than -60 dB until frequencies of MHz.


Palabras clave voltage reference, ultra-low power, picowatt, CMOS

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